

Please add the following new claims:

13. (New) A method for producing a semiconductor component in which at least one doped region is introduced into a semiconductor wafer, comprising the steps of:

- applying a solid glass layer provided with a dopant on at least one of two sides of the semiconductor wafer;
- heating the semiconductor wafer to a high temperature so that the dopant from the solid glass layer penetrates deep into the semiconductor wafer to produce the at least one doped region;
- removing the solid glass layer; and
- providing a dopant dosage of at least $10^{17}/\text{cm}^2$ in the at least one doped region.

14. (New) The method according to claim 13, wherein:
- the step of applying the solid glass layer is performed in accordance with a chemical vapor deposition operation.
15. (New) The method according to claim 14, wherein:
- the chemical vapor deposition operation is performed at atmospheric pressure.
16. (New) The method according to claim 13, wherein:
- the step of heating the semiconductor wafer is performed in an oxidizing atmosphere.
17. (New) The method according to claim 13, further comprising the step of:
- maintaining the high temperature for about 20 to 30 hours.
18. (New) The method according to claim 13, further comprising the step of:
- maintaining the high temperature for 21 hours.

19. (New) The method according to claim 13, wherein:

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the solid glass layer is applied both on a front side of the semiconductor wafer and on a back side of the semiconductor wafer, a doping type of the dopant on the back side being the same compared to a doping type of the dopant on the front side.

20. (New) The method according to claim 13, wherein:

the solid glass layer is applied both on a front side of the semiconductor wafer and on a back side of the semiconductor wafer, a doping type of the dopant on the back side being opposite compared to a doping type of the dopant on the front side.

21. (New) The method according to claim 13, wherein:

the solid glass layer has a dopant constituent of greater than 2 percentage by weight.

22. (New) The method according to claim 13, wherein:

the solid glass layer has a dopant constituent of about 3 to 6 percentage by weight.

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23. (New) The method according to claim 21, wherein:

the dopant constituent of the solid glass layer on a front side of the semiconductor wafer is different from the dopant constituent of the solid glass layer on a back side of the semiconductor wafer.

24. (New) The method according to claim 22, wherein:

the dopant constituent of the solid glass layer on a front side of the semiconductor wafer is different from the dopant constituent of the solid glass layer on a back side of the semiconductor wafer.

25. (New) The method according to claim 13, wherein:

the solid glass layer has a thickness of about 2 micrometers.

26. (New) The method according to claim 13, further comprising the steps of:

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applying a neutral glass layer on the solid glass layer prior to heating the semiconductor wafer; and

removing the neutral glass layer together with the solid glass layer after heating the semiconductor wafer.

27. (New) The method according to claim 26, wherein:

the neutral glass layer has a thickness of about 0.5 micrometers.

28. (New) The method according to claim 13, wherein:

the step of removing the solid glass layer is performed in accordance with hydrofluoric acid.

Remarks

This Preliminary Amendment cancels original claims 1 to 12, without prejudice, and cancels substitute claim 1, without prejudice, in the underlying PCT Application No. PCT/DE00/00546. The Preliminary Amendment also adds new claims 13-28. The new claims conform the claims to U.S. Patent and Trademark Office rules and do not add new matter to the application.

In accordance with 37 C.F.R. § 1.121(b)(3), the Substitute Specification (including the Abstract, but without the claims) contains no new matter. The amendments reflected in the Substitute Specification (including Abstract) are to conform the Specification and Abstract to U.S. Patent and Trademark Office rules or to correct informalities. As required by 37 C.F.R. § 1.121(b)(3)(iii) and § 1.125(b)(2), a Marked Up Version Of The Substitute Specification comparing the Specification of record and the Substitute Specification also accompanies this Preliminary Amendment. Approval and entry of the Substitute Specification (including Abstract) are respectfully requested.

The underlying PCT Application No. PCT/DE00/00546 includes an International Search Report, dated October 17, 2000, and an International Preliminary Examination Report, dated May 25, 2001, copies of which are submitted herewith.